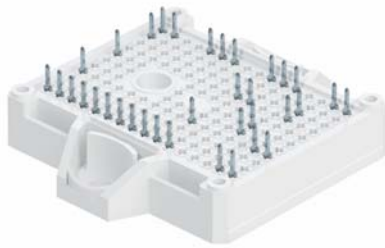


SK25DGDL12T7ETE2s



SEMITOP®E2 Solder

3-phase Converter-Inverter-Brake (CIB)

SK25DGDL12T7ETE2s

Features*

- Optimized design for superior thermal performance
- Low inductive design
- Solder contact technology
- 1200V Generation 7 IGBT (T7)
- Robust and soft switching CAL4F diode technology
- PEP rectifier diode technology for enhanced power and environmental robustness
- Integrated NTC temperature sensor
- UL recognized file no. E 63 532

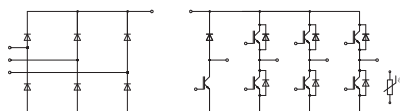
Typical Applications

- Motor drives
- Air conditioning
- Auxiliary Inverters

Remarks

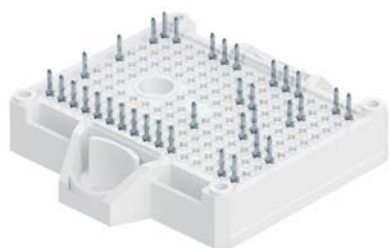
- Recommended $T_{j,op} = -40 \dots +150 \text{ }^{\circ}\text{C}$
- $T_{j,op} > 150 \text{ }^{\circ}\text{C}$ during overload (details on AN19-002)

Absolute Maximum Ratings				
Symbol	Conditions		Values	Unit
Inverter - IGBT				
V _{CES}	T _j = 25 °C		1200	V
I _C	λ _{paste} =0.8 W/(mK)	T _s = 70 °C	33	A
	T _j = 175 °C	T _s = 100 °C	27	A
I _C	λ _{paste} =2.5 W/(mK)	T _s = 70 °C	38	A
	T _j = 175 °C	T _s = 100 °C	31	A
I _{Cnom}			25	A
I _{CRM}			50	A
V _{GES}			-20 ... 20	V
t _{psc}	V _{CC} = 800 V V _{GE} ≤ 15 V V _{CES} ≤ 1200 V	T _j = 175 °C	7	μs
T _j			-40 ... 175	°C
Chopper - IGBT				
V _{CES}	T _j = 25 °C		1200	V
I _C	λ _{paste} =0.8 W/(mK)	T _s = 70 °C	33	A
	T _j = 175 °C	T _s = 100 °C	27	A
I _C	λ _{paste} =2.5 W/(mK)	T _s = 70 °C	38	A
	T _j = 175 °C	T _s = 100 °C	31	A
I _{Cnom}			25	A
I _{CRM}			50	A
V _{GES}			-20 ... 20	V
t _{psc}	V _{CC} = 800 V V _{GE} ≤ 15 V V _{CES} ≤ 1200 V	T _j = 175 °C	7	μs
T _j			-40 ... 175	°C
Inverse - Diode				
V _{RRM}	T _j = 25 °C		1200	V
I _F	λ _{paste} =0.8 W/(mK)	T _s = 70 °C	24	A
	T _j = 175 °C	T _s = 100 °C	20	A
I _F	λ _{paste} =2.5 W/(mK)	T _s = 70 °C	28	A
	T _j = 175 °C	T _s = 100 °C	23	A
I _{FRM}			50	A
I _{FSM}	t _p = 10 ms, sin 180°, T _j = 150 °C		100	A
T _j			-40 ... 175	°C
Freewheeling - Diode				
V _{RRM}	T _j = 25 °C		1200	V
I _F	λ _{paste} =0.8 W/(mK)	T _s = 70 °C	12	A
	T _j = 175 °C	T _s = 100 °C	10	A
I _F	λ _{paste} =2.5 W/(mK)	T _s = 70 °C	13	A
	T _j = 175 °C	T _s = 100 °C	11	A
I _{FRM}			20	A
I _{FSM}	t _p = 10 ms, sin 180°, T _j = 150 °C		36	A
T _j			-40 ... 175	°C



DGDLET

SK25DGDL12T7ETE2s



SEMISTOP® E2 Solder

3-phase
Converter-Inverter-Brake
(CIB)

SK25DGDL12T7ETE2s

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- Optimized design for superior thermal performance
- Low inductive design
- Solder contact technology
- 1200V Generation 7 IGBT (T7)
- Robust and soft switching CAL4F diode technology
- PEP rectifier diode technology for enhanced power and environmental robustness
- Integrated NTC temperature sensor
- UL recognized file no. E 63 532

Typical Applications

- Motor drives
- Air conditioning
- Auxiliary Inverters

Remarks

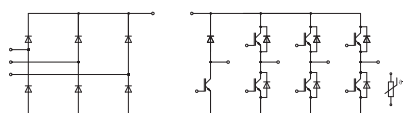
- Recommended $T_{j,op} = -40 \dots +150 \text{ }^{\circ}\text{C}$
- $T_{j,op} > 150 \text{ }^{\circ}\text{C}$ during overload (details on AN19-002)

Absolute Maximum Ratings

Symbol	Conditions		Values	Unit
Rectifier - Diode				
V _{RRM}	T _j = 25 °C		1600	V
I _F	λ _{paste} =0.8 W/(mK)	T _s = 70 °C	47	A
	T _j = 175 °C	T _s = 100 °C	37	A
I _F	λ _{paste} =2.5 W/(mK)	T _s = 70 °C	57	A
	T _j = 175 °C	T _s = 100 °C	45	A
I _{FSM}	t _p = 10 ms	T _j = 25 °C	370	A
	sin 180°	T _j = 150 °C	270	A
i ² t	t _p = 10 ms	T _j = 25 °C	685	A ² s
	sin 180°	T _j = 150 °C	365	A ² s
T _j			-40 ... 175	°C
Module				
I _{t(RMS)}	, ΔT _{terminal} at PCB joint = 30 K, per pin		30	A
T _{stg}	module without TIM		-40 ... 125	°C
V _{isol}	AC, sinusoidal, 1 min		2500	V

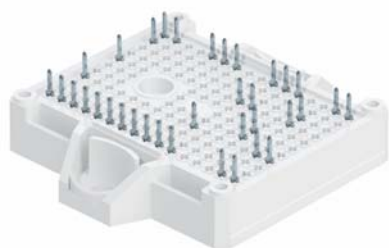
Characteristics

Symbol	Conditions		min.	typ.	max.	Unit
Inverter - IGBT						
V _{CE(sat)}	I _C = 25 A	T _j = 25 °C		1.60	1.75	V
	V _{GE} = 15 V	T _j = 150 °C		1.78	1.93	V
	chiplevel	T _j = 175 °C		1.82	1.97	V
V _{CE0}		T _j = 25 °C		1.00	1.05	V
	chiplevel	T _j = 150 °C		0.80	0.85	V
		T _j = 175 °C		0.75	0.80	V
r _{CE}	V _{GE} = 15 V	T _j = 25 °C		24	28	mΩ
	chiplevel	T _j = 150 °C		39	43	mΩ
		T _j = 175 °C		43	47	mΩ
V _{GE(th)}	V _{GE} = V _{CE} , I _C = 0.53 mA		5.15	5.8	6.45	V
I _{CES}	V _{GE} = 0 V, V _{CE} = 1200 V, T _j = 25 °C				1	mA
C _{ies}	V _{CE} = 25 V V _{GE} = 0 V	f = 1 MHz		4.80		nF
C _{oes}		f = 1 MHz		0.06		nF
C _{res}		f = 1 MHz		0.02		nF
Q _G	V _{GE} = -15 V ... +15 V			354		nC
R _{Gint}	T _j = 25 °C			0		Ω
t _{d(on)}	V _{CC} = 600 V I _C = 25 A R _{G on} = 6.2 Ω	T _j = 25 °C		28		ns
		T _j = 150 °C		30		ns
		T _j = 175 °C		32		ns
t _r	R _{G off} = 6.2 Ω V _{GE} = +15/-15 V	T _j = 25 °C		23		ns
		T _j = 150 °C		25		ns
		T _j = 175 °C		26		ns
E _{on}	(T _j = 150 °C) di/dt _{on} = 880 A/μs	T _j = 25 °C		1.65		mJ
	di/dt _{off} = 210 A/μs	T _j = 150 °C		2.42		mJ
	dv/dt = 5400 V/μs	T _j = 175 °C		2.72		mJ



DGDLE-T

SK25DGDL12T7ETE2s



SEMITOP®E2 Solder

3-phase Converter-Inverter-Brake (CIB)

SK25DGDL12T7ETE2s

Features*

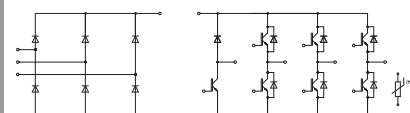
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- Low inductive design
- Solder contact technology
- 1200V Generation 7 IGBT (T7)
- Robust and soft switching CAL4F diode technology
- PEP rectifier diode technology for enhanced power and environmental robustness
- Integrated NTC temperature sensor
- UL recognized file no. E 63 532

Typical Applications

- Motor drives
- Air conditioning
- Auxiliary Inverters

Remarks

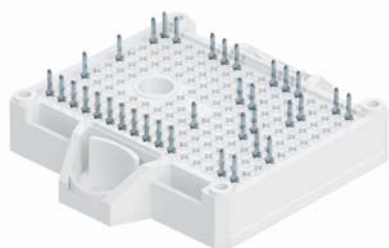
- Recommended $T_{j,op} = -40 \dots +150 \text{ }^{\circ}\text{C}$
- $T_{j,op} > 150 \text{ }^{\circ}\text{C}$ during overload (details on AN19-002)



DGDL-ET

Characteristics						
Symbol	Conditions		min.	typ.	max.	Unit
Inverter - IGBT						
t _{d(off)}	V _{CC} = 600 V	T _j = 25 °C		191		ns
	I _C = 25 A	T _j = 150 °C		231		ns
	R _{G on} = 6.2 Ω	T _j = 175 °C		251		ns
t _f	R _{G off} = 6.2 Ω	T _j = 25 °C		66		ns
	V _{GE} = +15/-15 V	T _j = 150 °C		101		ns
	(T _j = 150 °C)	T _j = 175 °C		108		ns
E _{off}	di/dt _{on} = 880 A/μs	T _j = 25 °C		2.04		mJ
	di/dt _{off} = 210 A/μs	T _j = 150 °C		2.71		mJ
	dv/dt = 5400 V/μs	T _j = 175 °C		3.09		mJ
R _{th(j-s)}	per IGBT, λ _{paste} =0.8 W/(mK)			1.32		K/W
R _{th(j-s)}	per IGBT, λ _{paste} =2.5 W/(mK)			1.06		K/W
Chopper - IGBT						
V _{CE(sat)}	I _C = 25 A	T _j = 25 °C		1.60	1.75	V
	V _{GE} = 15 V	T _j = 150 °C		1.78	1.93	V
	chipselevel	T _j = 175 °C		1.82	1.97	V
V _{CE0}		T _j = 25 °C		1.00	1.05	V
	chipselevel	T _j = 150 °C		0.80	0.85	V
		T _j = 175 °C		0.75	0.80	V
r _{CE}	V _{GE} = 15 V	T _j = 25 °C		24	28	mΩ
	chipselevel	T _j = 150 °C		39	43	mΩ
		T _j = 175 °C		43	47	mΩ
V _{GE(th)}	V _{GE} = V _{CE} , I _C = 0.53 mA		5.15	5.8	6.45	V
I _{CES}	V _{GE} = 0 V, V _{CE} = 1200 V, T _j = 25 °C				1	mA
C _{ies}	V _{CE} = 25 V	f = 1 MHz		4.80		nF
C _{oes}	V _{GE} = 0 V	f = 1 MHz		0.06		nF
C _{res}		f = 1 MHz		0.02		nF
Q _G	V _{GE} = -15 V ... +15 V			354		nC
R _{Gint}	T _j = 25 °C			0		Ω
t _{d(on)}		T _j = 25 °C		28		ns
		T _j = 150 °C		30		ns
		T _j = 175 °C		32		ns
t _r		T _j = 25 °C		23		ns
		T _j = 150 °C		25		ns
		T _j = 175 °C		26		ns
E _{on}	V _{CC} = 600 V	T _j = 25 °C		1.65		mJ
	I _C = 25 A	T _j = 150 °C		2.42		mJ
	R _{G on} = 6.2 Ω	T _j = 175 °C		2.72		mJ
	R _{G off} = 6.2 Ω					
	V _{GE} = +15/-15 V					
t _{d(off)}		T _j = 25 °C		191		ns
	(T _j = 150 °C)	T _j = 150 °C		231		ns
	di/dt _{on} = 880 A/μs	T _j = 175 °C		251		ns
t _f	di/dt _{off} = 210 A/μs	T _j = 25 °C		66		ns
	dv/dt = 5400 V/μs	T _j = 150 °C		101		ns
		T _j = 175 °C		108		ns
E _{off}		T _j = 25 °C		2.04		mJ
		T _j = 150 °C		2.71		mJ
		T _j = 175 °C		3.09		mJ
R _{th(j-s)}	per IGBT, λ _{paste} =0.8 W/(mK)			1.32		K/W
R _{th(j-s)}	per IGBT, λ _{paste} =2.5 W/(mK)			1.06		K/W

SK25DGDL12T7ETE2s



SEMITOP®E2 Solder

3-phase Converter-Inverter-Brake (CIB)

SK25DGDL12T7ETE2s

Features*

- Optimized design for superior thermal performance
- Low inductive design
- Solder contact technology
- 1200V Generation 7 IGBT (T7)
- Robust and soft switching CAL4F diode technology
- PEP rectifier diode technology for enhanced power and environmental robustness
- Integrated NTC temperature sensor
- UL recognized file no. E 63 532

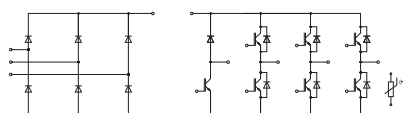
Typical Applications

- Motor drives
- Air conditioning
- Auxiliary Inverters

Remarks

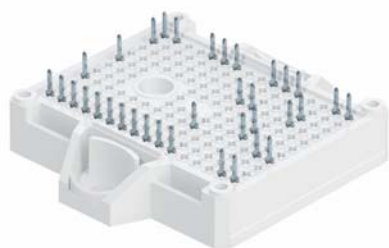
- Recommended $T_{j,op} = -40 \dots +150 \text{ }^{\circ}\text{C}$
- $T_{j,op} > 150 \text{ }^{\circ}\text{C}$ during overload (details on AN19-002)

Characteristics						
Symbol	Conditions		min.	typ.	max.	Unit
Inverse - Diode						
V _F = V _{EC}	I _F = 25 A	T _j = 25 °C		2.41	2.74	V
		T _j = 150 °C		2.45	2.79	V
		chiplevel	T _j = 175 °C		2.30	2.62
V _{F0}	chiplevel	T _j = 25 °C		1.30	1.50	V
		T _j = 150 °C		0.90	1.10	V
		T _j = 175 °C		0.82	0.98	V
r _F	chiplevel	T _j = 25 °C		44	50	mΩ
		T _j = 150 °C		62	68	mΩ
		T _j = 175 °C		59	66	mΩ
I _{RRM}	V _{CC} = 600 V I _F = 25 A V _{GE} = -15 V (T _j = 150 °C) di/dt _{off} = 1050 A/μs	T _j = 25 °C		20		A
		T _j = 150 °C		28		A
		T _j = 175 °C		30		A
Q _{rr}		T _j = 25 °C		1.41		μC
		T _j = 150 °C		3.71		μC
		T _j = 175 °C		4.19		μC
E _{rr}		T _j = 25 °C		0.51		mJ
		T _j = 150 °C		1.61		mJ
		T _j = 175 °C		2.46		mJ
R _{th(j-s)}	per Diode, λ _{paste} =0.8 W/(mK)			1.66		K/W
R _{th(j-s)}	per Diode, λ _{paste} =2.5 W/(mK)			1.29		K/W
Freewheeling - Diode						
V _F = V _{EC}	I _F = 10 A	T _j = 25 °C		2.59	2.94	V
		T _j = 150 °C		2.71	3.08	V
		chiplevel	T _j = 175 °C		2.53	2.89
V _{F0}	chiplevel	T _j = 25 °C		1.30	1.50	V
		T _j = 150 °C		0.90	1.10	V
		T _j = 175 °C		0.82	0.98	V
r _F	chiplevel	T _j = 25 °C		129	144	mΩ
		T _j = 150 °C		181	198	mΩ
		T _j = 175 °C		171	191	mΩ
I _{RRM}	V _{CC} = 600 V I _F = 10 A V _{GE} = -15 V (T _j = 150 °C) di/dt _{off} = 790 A/μs	T _j = 25 °C		8		A
		T _j = 150 °C		14		A
		T _j = 175 °C		16		A
Q _{rr}		T _j = 25 °C		0.58		μC
		T _j = 150 °C		2.01		μC
		T _j = 175 °C		2.37		μC
E _{rr}		T _j = 25 °C		0.36		mJ
		T _j = 150 °C		0.91		mJ
		T _j = 175 °C		1.16		mJ
R _{th(j-s)}	per Diode, λ _{paste} =0.8 W/(mK)			2.64		K/W
R _{th(j-s)}	per Diode, λ _{paste} =2.5 W/(mK)			2.24		K/W



DGDLET

SK25DGDL12T7ETE2s



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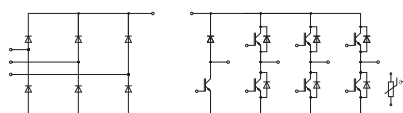
Typical Applications

- Motor drives
- Air conditioning
- Auxiliary Inverters

Remarks

- Recommended $T_{j,op} = -40 \dots +150 \text{ }^{\circ}\text{C}$
- $T_{j,op} > 150 \text{ }^{\circ}\text{C}$ during overload (details on AN19-002)

Characteristics						
Symbol	Conditions		min.	typ.	max.	Unit
Rectifier - Diode						
V _F	I _F = 25 A chiplevel	T _j = 25 °C		1.04	1.30	V
		T _j = 150 °C		0.95	1.21	V
		T _j = 175 °C		0.94	1.21	V
V _{F0}	chiplevel	T _j = 25 °C		0.89	1.09	V
		T _j = 150 °C		0.73	0.92	V
		T _j = 175 °C		0.69	0.88	V
r _F	chiplevel	T _j = 25 °C		6.2	8.5	mΩ
		T _j = 150 °C		8.8	12	mΩ
		T _j = 175 °C		10.0	13	mΩ
I _R	T _j = 150 °C, V _{RRM}				2	mA
R _{th(j-s)}	per Diode, λ _{paste} =0.8 W/(mK)			1.48		K/W
R _{th(j-s)}	per Diode, λ _{paste} =2.5 W/(mK)			1.14		K/W
Module						
M _s	to heatsink		1.6		2.3	Nm
w				35		g
L _{CE}				30		nH
Temperature Sensor						
R ₁₀₀	T _c =100°C (R ₂₅ =5 kΩ)			493 ± 5%		Ω
B _{25/85}	R _(T) =R ₂₅ *exp[B _{25/85} *(1/T-1/298)], T[K]			3420		K



DGDLE-T

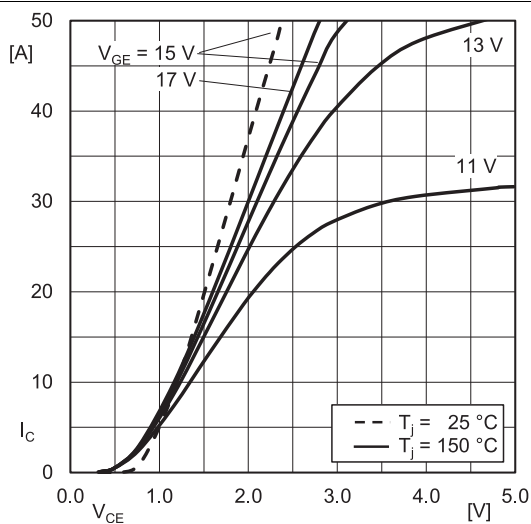


Fig. 1: Typ. IGBT output characteristic, incl. $R_{CC+EE'}$

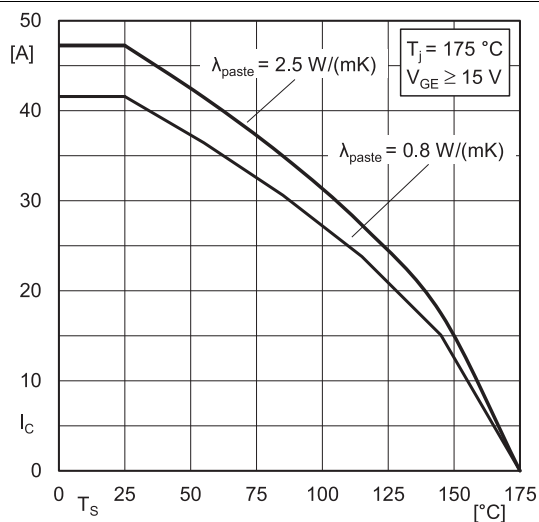


Fig. 2: IGBT rated current vs. temperature $I_C=f(T_s)$

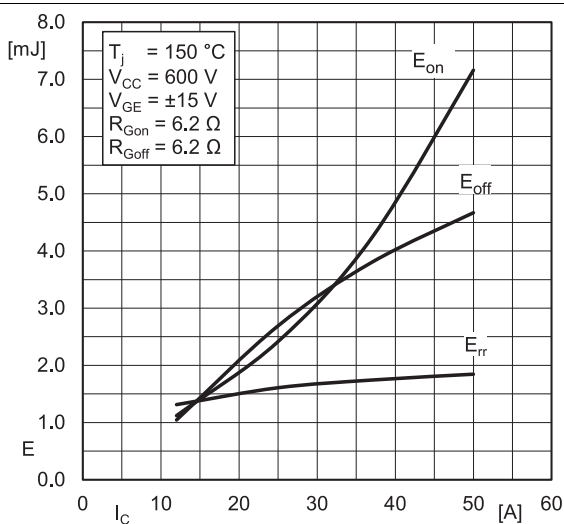


Fig. 3: Typ. turn-on /-off energy = $f(I_C)$

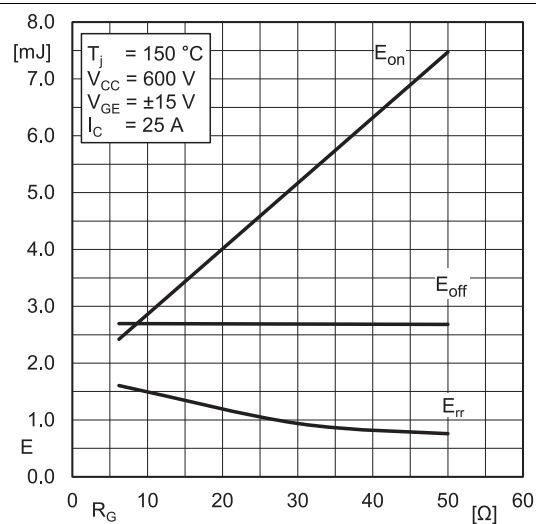


Fig. 4: Typ. turn-on /-off energy = $f(R_G)$

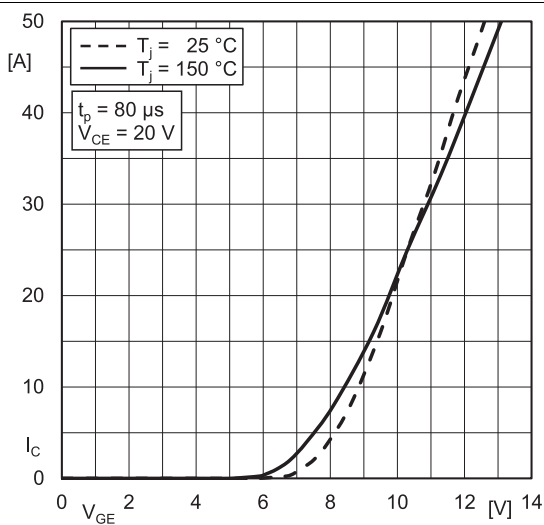


Fig. 5: Typ. IGBT transfer characteristic

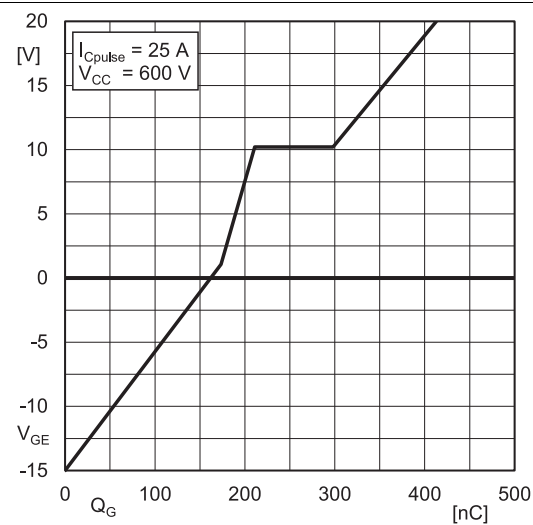


Fig. 6: Typ. IGBT gate charge characteristic

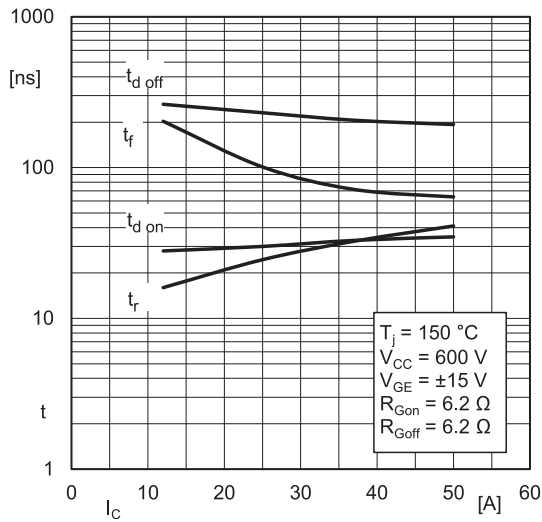


Fig. 7: Typ. switching times = f(I_C)

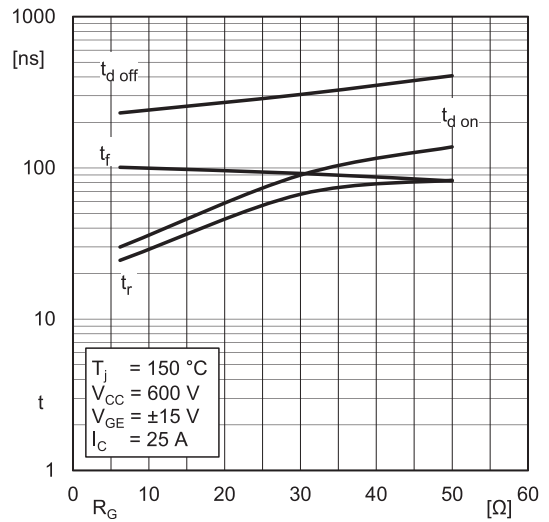


Fig. 8: Typ. switching times = f(R_G)

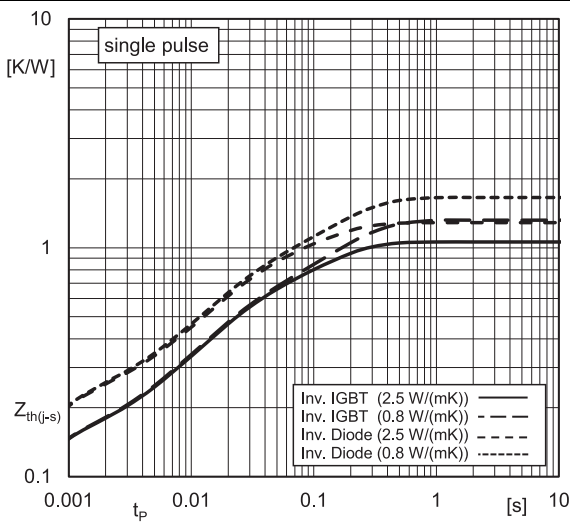


Fig. 9: Typ. transient thermal impedance

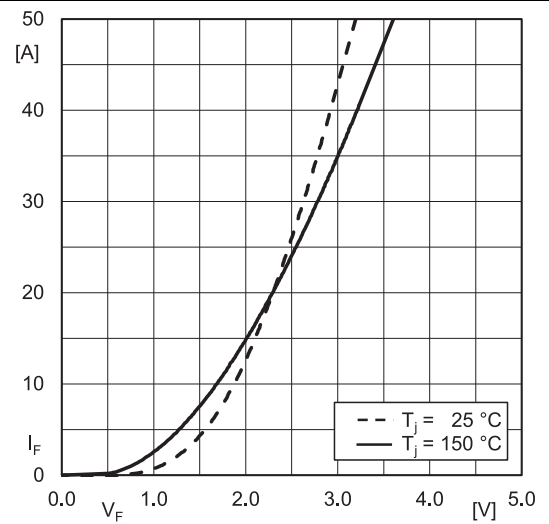


Fig. 10: Typ. Inv. diode forward charact., incl. R_{GG}+EE'

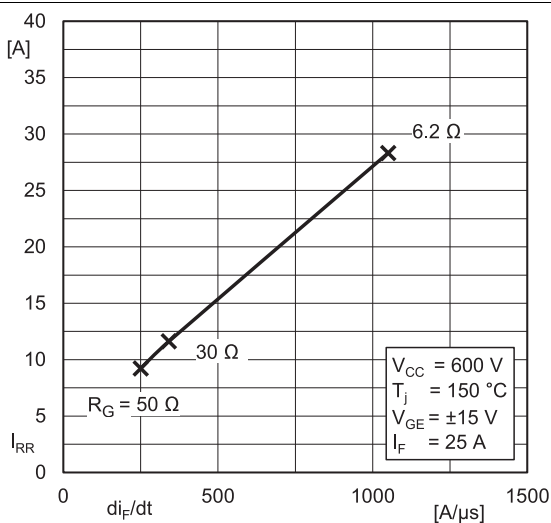


Fig. 11: Typ. Inv. diode peak reverse recovery current

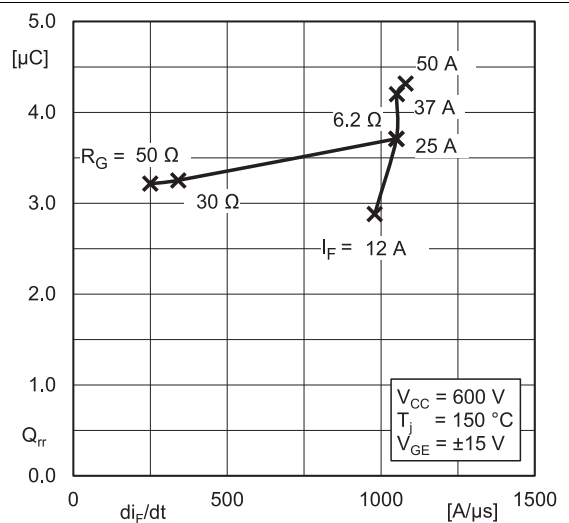


Fig. 12: Typ. Inv. diode reverse recovery charge

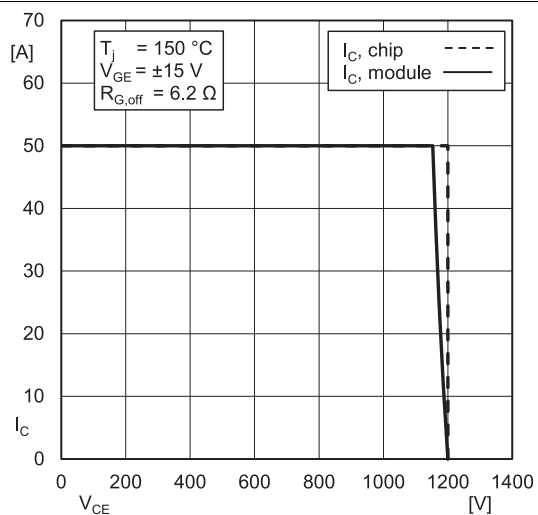


Fig. 13: IGBT Reverse Bias Safe Operating Area (RBSOA)

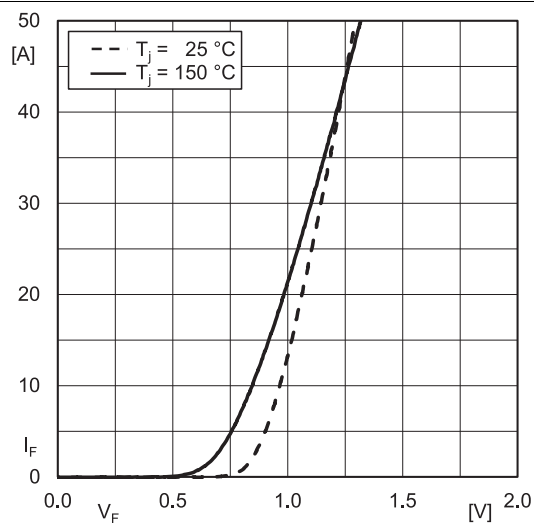
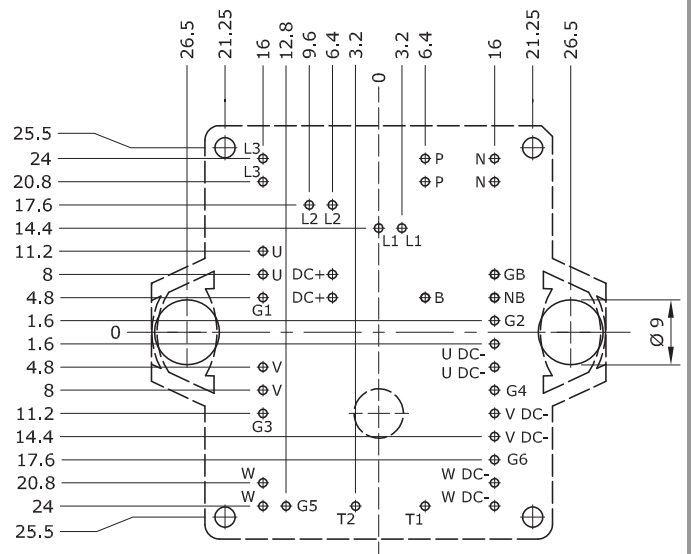
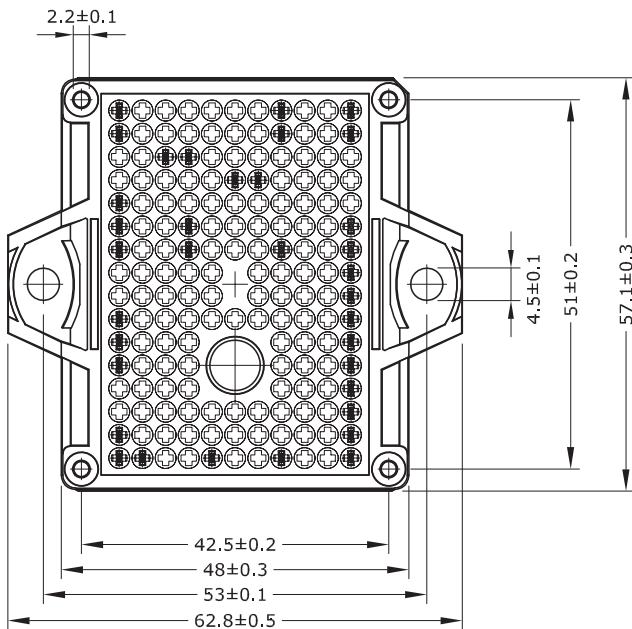
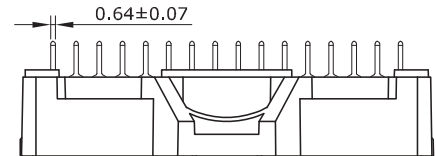
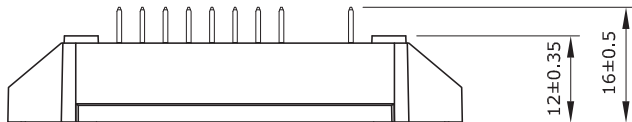


Fig. 14: Typ. Rect. diode forward charact., incl. $R_{CC'+EE'}$

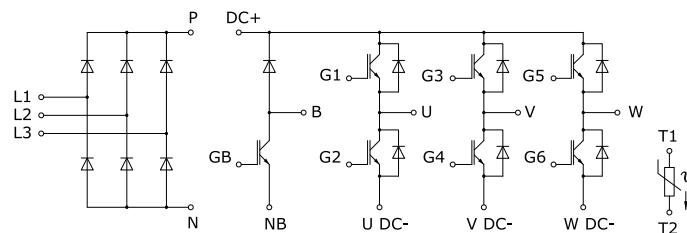
SK25DGDL12T7ETE2s



- Pin-Grid 3.2 mm

- Tolerance of pinpositions $\Phi 0.4$

SEMITOP®E2 Solder



DGDL-ET

This is an electrostatic discharge sensitive device (ESDS) due to international standard IEC 61340.

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